



STD35NF06L

N-CHANNEL 60V - 0.014 Ω - 35A DPAK STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD35NF06L	60 V	< 0.017 Ω	35 A

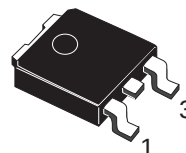
- TYPICAL R_{DS(on)} = 0.014 Ω
- LOW THRESHOLD DRIVE
- GATE CHARGE MINIMIZED
- SURFACE-MOUNTING DPAK (TO-252)
POWER PACKAGE IN TAPE & REEL
(SUFFIX "T4")

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

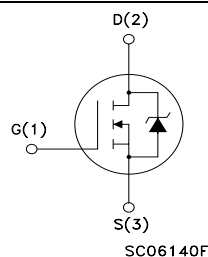
APPLICATIONS

- DC-AC CONVERTERS
- AUTOMOTIVE SWITCHING APPLICATION



**DPAK
TO-252**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



Ordering Information

SALES TYPE	MARKING	PACKAGE	PACKAGING
STD35NF06LT4	D35NF06L	TO-252	TAPE & REEL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	60	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C	35	A
I _D	Drain Current (continuous) at T _C = 100°C	24.5	A
I _{DM} (●)	Drain Current (pulsed)	140	A
P _{tot}	Total Dissipation at T _C = 25°C	80	W
	Derating Factor	0.67	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	280	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(●) Pulse width limited by safe operating area.

(1) I_{SD} $\leq$ 35A, di/dt $\leq$ 100A/ μ s, V_{DD} $\leq$ V(BR)_{DSS}, T_j $\leq$ T_{JMAX}
(2) Starting T_j = 25 °C, I_D = 30A, V_{DD} = 30V

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1.88	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	100	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose (1.6 mm from case, for 10 sec)	Max	275	°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 17.5 A V _{GS} = 4.5 V I _D = 17.5 A		0.014 0.016	0.017 0.020	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 17.5 A		28		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		1700 305 105		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 27.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		20 100		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48\text{ V}$ $I_D = 55\text{ A}$ $V_{GS} = 4.5\text{ V}$		25 5 10	33	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 30\text{ V}$ $I_D = 27.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		40 20		ns ns

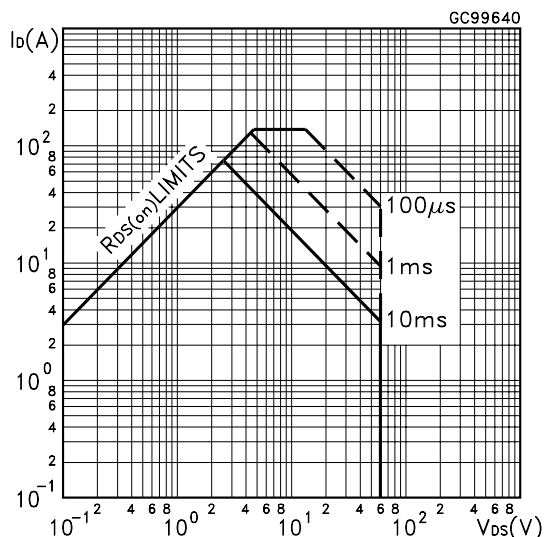
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				35 140	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 35\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 35\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		80 200 5		ns nC A

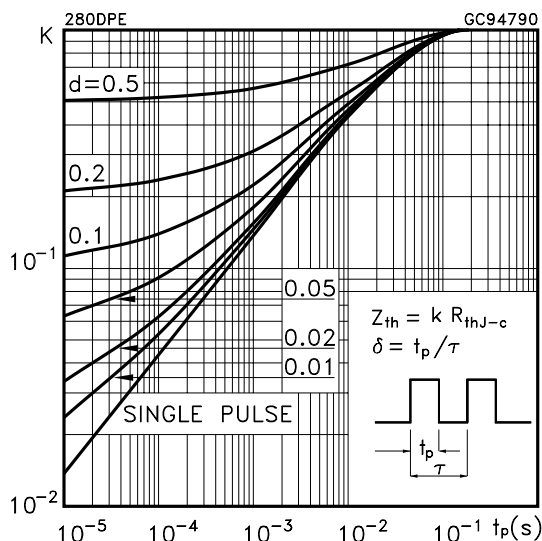
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

($\bullet$) Pulse width limited by safe operating area.

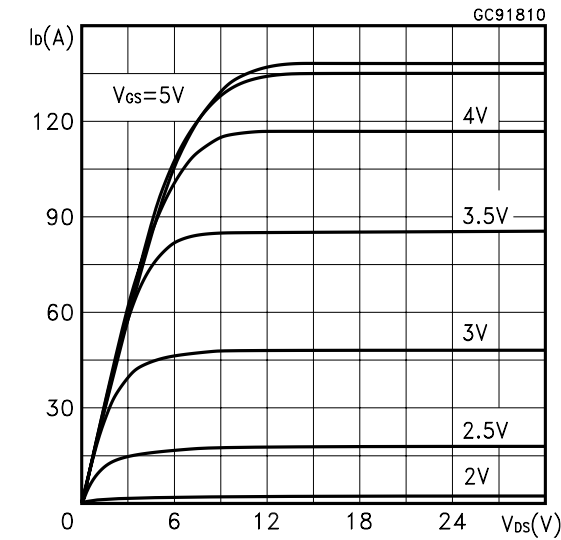
Safe Operating Area



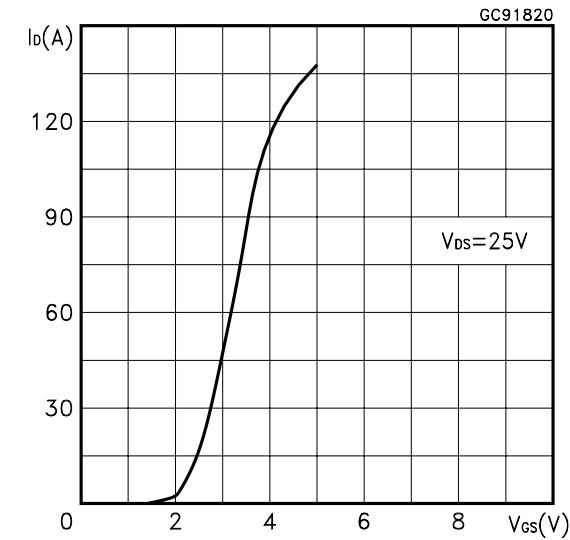
Thermal Impedance



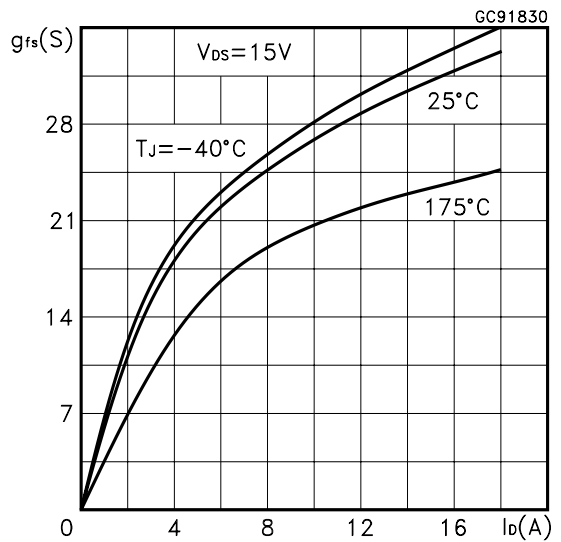
Output Characteristics



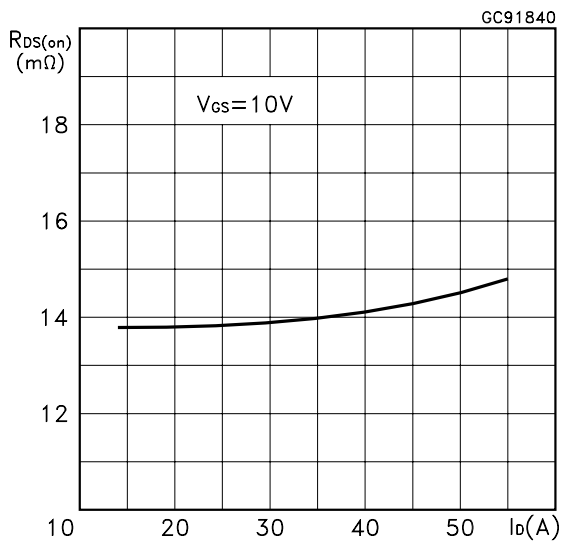
Transfer Characteristics



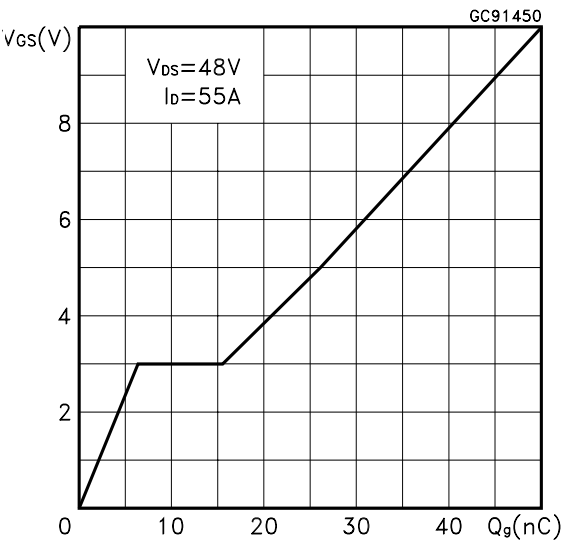
Transconductance



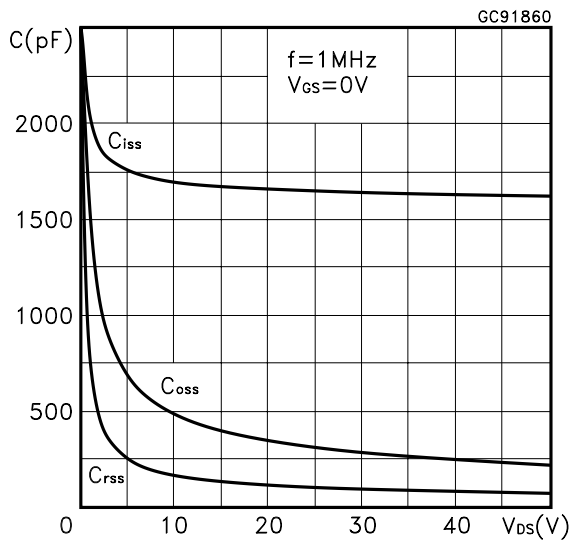
Static Drain-source On Resistance



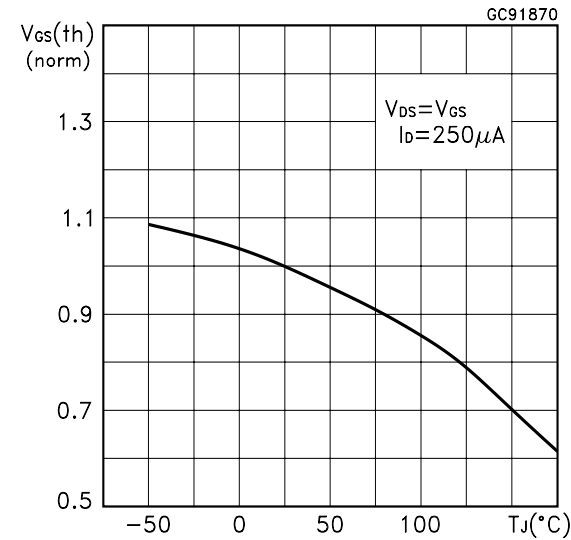
Gate Charge vs Gate-source Voltage



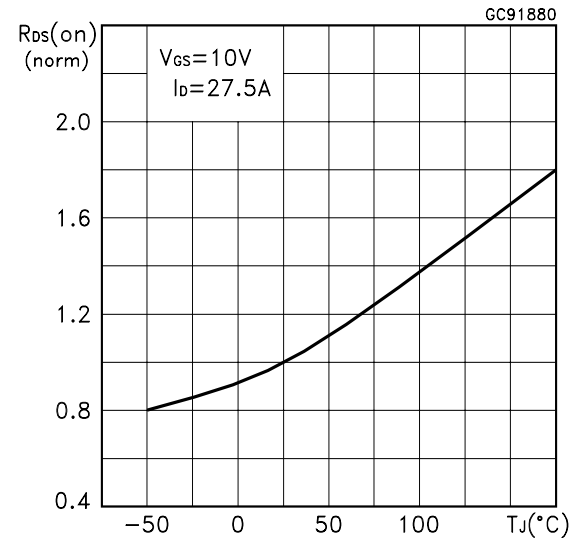
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics

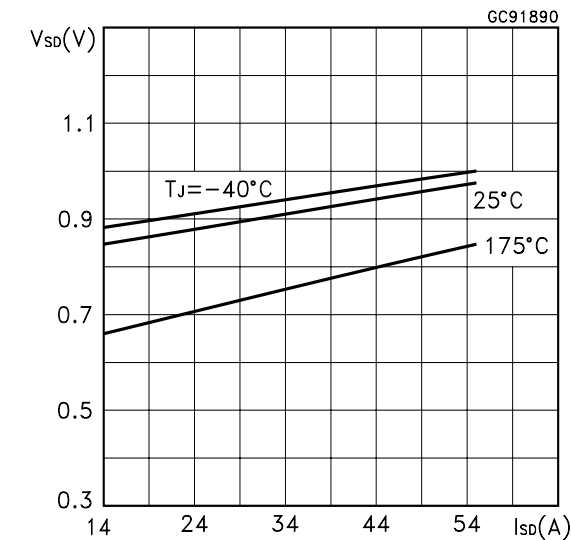


Fig. 1: Unclamped Inductive Load Test Circuit

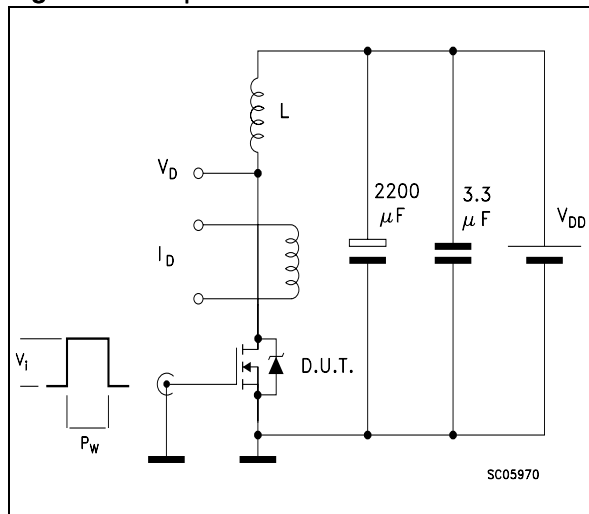


Fig. 2: Unclamped Inductive Waveform

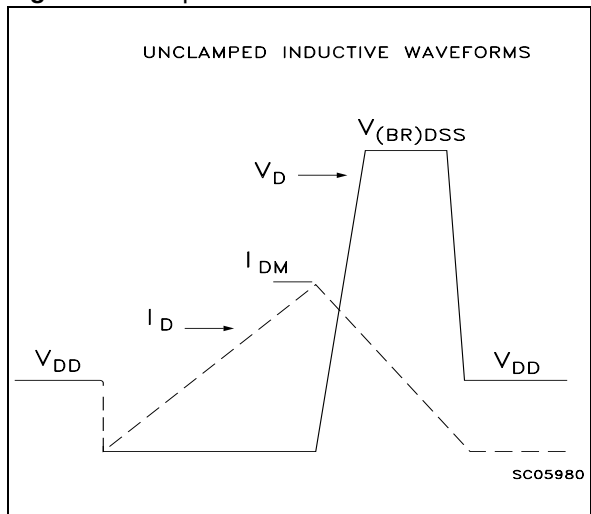


Fig. 3: Switching Times Test Circuits For Resistive Load

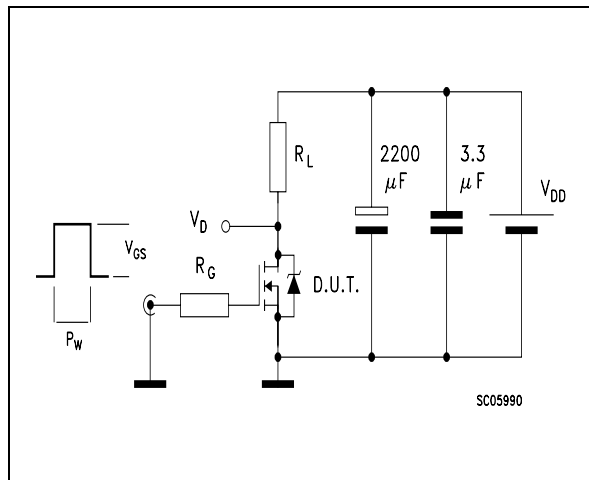


Fig. 4: Gate Charge test Circuit

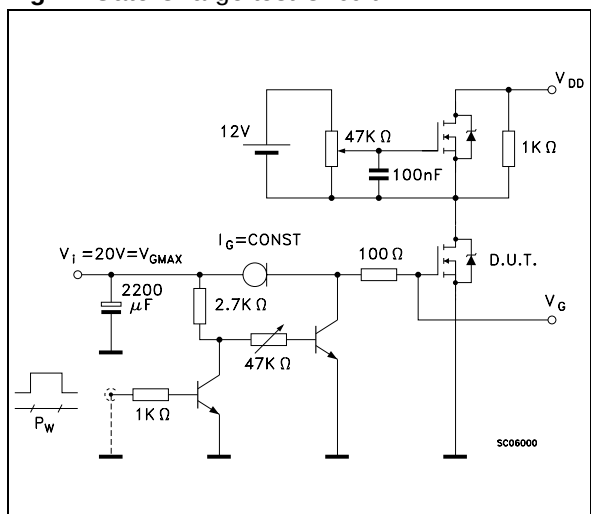
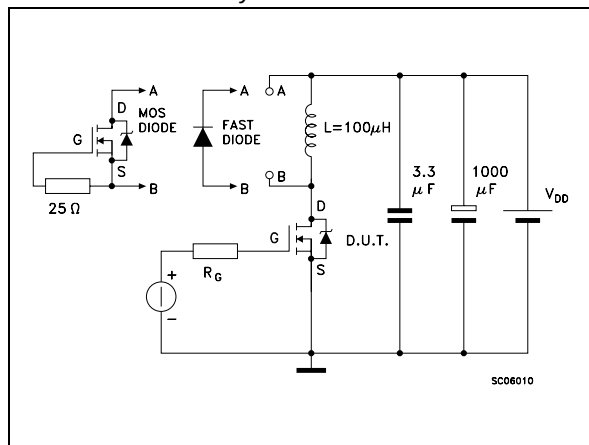
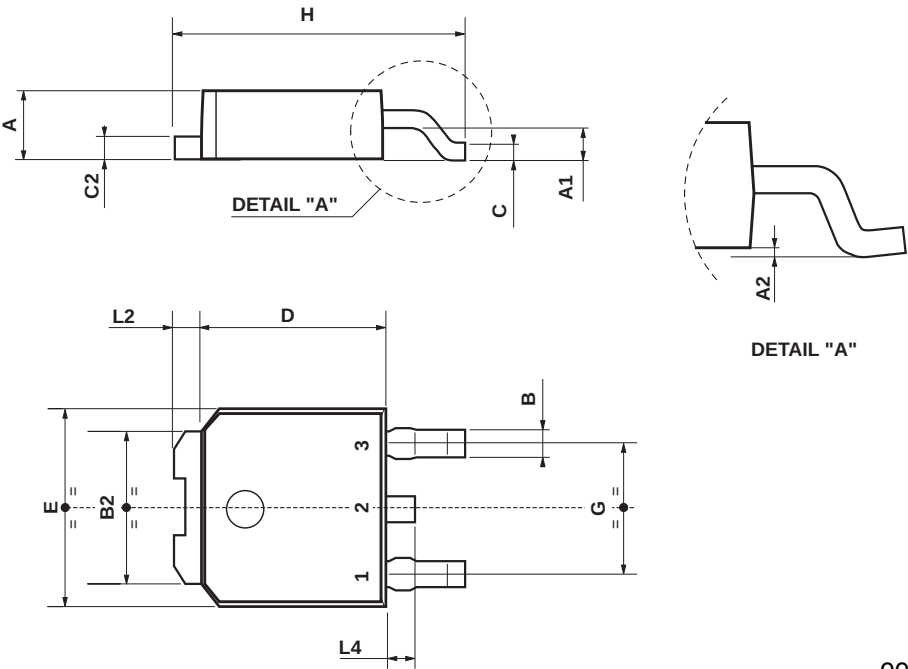


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

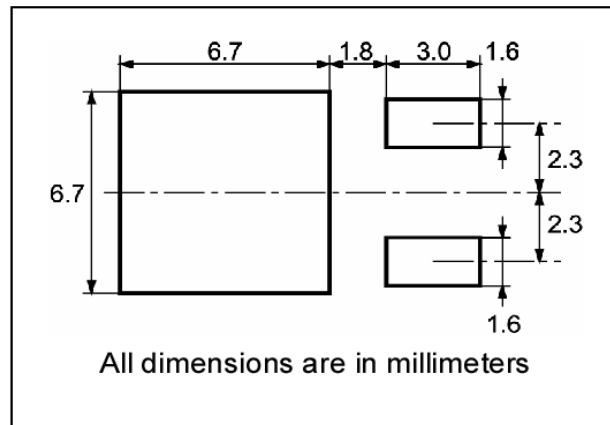
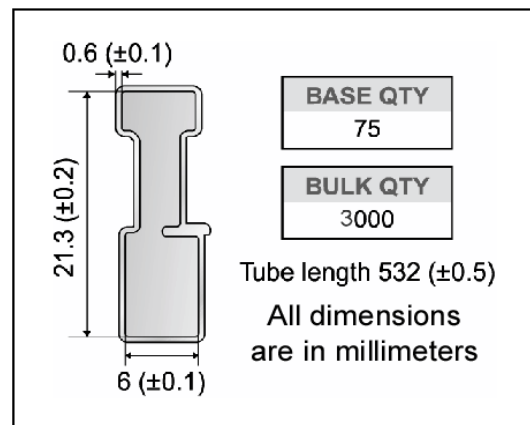
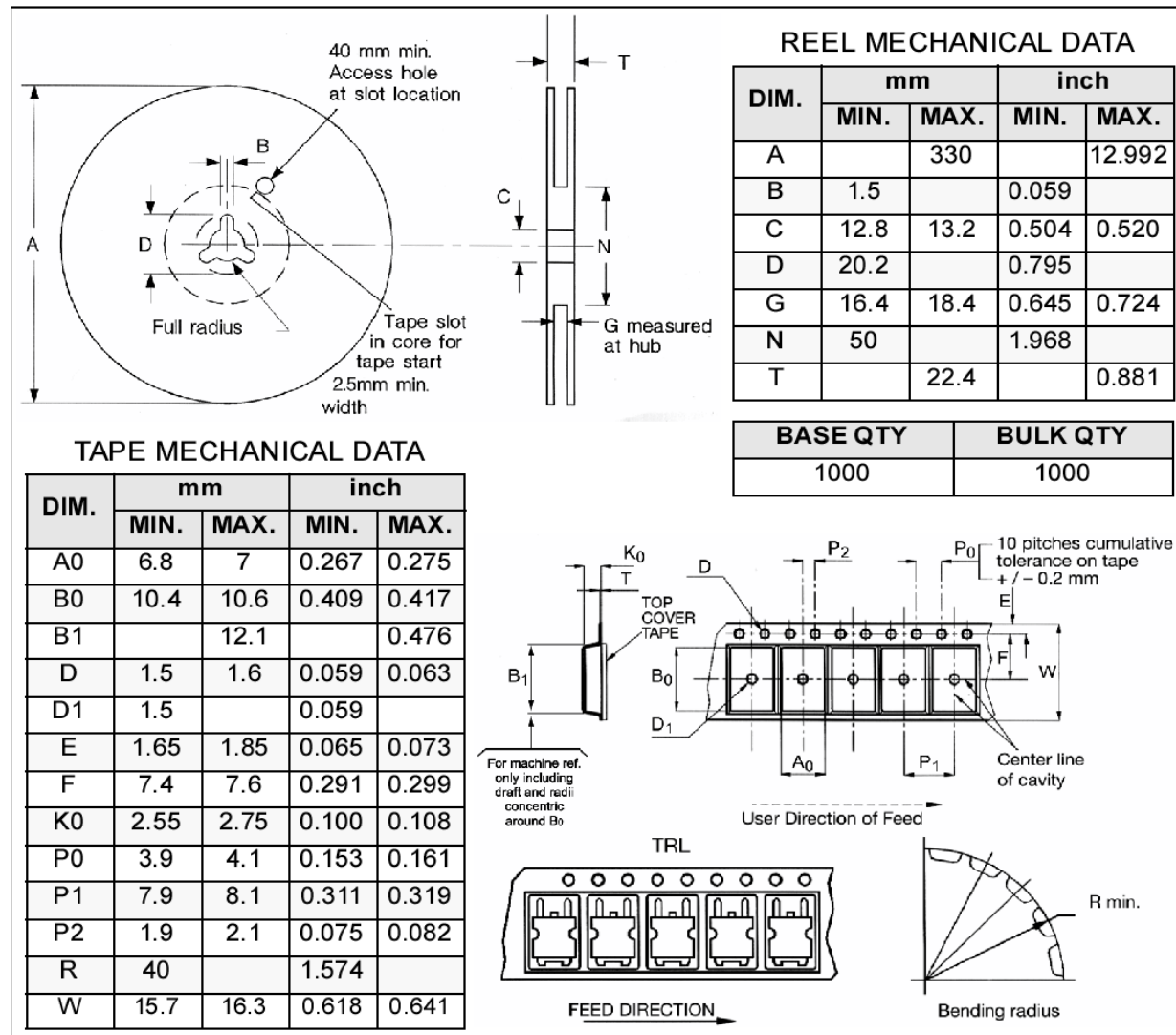


TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



0068772-B

DPAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

*on sales type

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